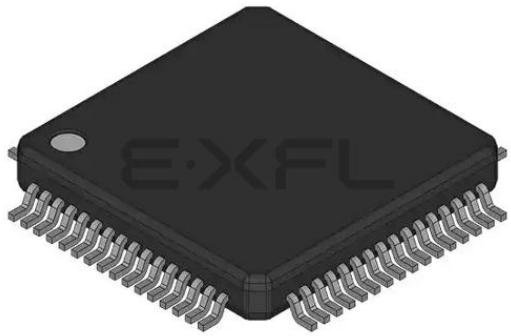
Renesas Electronics America Inc - R5F2LA68ANFP#V0 Datasheet



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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	I²C, LINbus, SIO, SSU, UART/USART
Peripherals	LCD, POR, PWM, Voltage Detect, WDT
Number of I/O	56
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	3.5K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 5.5V
Data Converters	A/D 8x10b
Oscillator Type	Internal
Operating Temperature	-20°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f2la68anfp-v0

Table 1.2 Programmable I/O Ports Provided for Each Group (R8C/LA3A Group, R8C/LA5A Group)

Programmable I/O Port	R8C/LA3A Group Total: 26 I/O pins								R8C/LA5A Group Total: 44 I/O pins							
	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
P0	—	—	—	—	—	—	—	—	✓	✓	✓	✓	✓	✓	✓	✓
P2	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓
P3	—	—	—	—	—	—	—	—	✓	✓	✓	✓	✓	✓	✓	✓
P5	—	✓	✓	✓	✓	✓	✓	✓	—	✓	✓	✓	✓	✓	✓	✓
P7	—	—	—	—	—	—	✓	—	—	—	—	—	—	✓	✓	✓
P8	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓
P9	—	—	—	—	—	—	✓	✓	—	—	—	—	—	—	✓	✓

Notes:
1. The symbol "✓" indicates a programmable I/O port.
2. The symbol "—" indicates the settings should be made as follows:
   - Set 0 to the corresponding bits in the PDi (i = 0, 3, 5, 7, 9) register. When read, the content is 0.
   - Set 0 to the corresponding bits in the Pi (i = 0, 3, 5, 7, 9) register. When read, the content is 0.

Table 1.3 Programmable I/O Ports Provided for Each Group (R8C/LA6A Group, R8C/LA8A Group)

Programmable I/O Port	R8C/LA6A Group Total: 56 I/O pins								R8C/LA8A Group Total: 72 I/O pins							
	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0	Bit 7	Bit 6	Bit 5	Bit 4	Bit 3	Bit 2	Bit 1	Bit 0
P0	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓
P1	✓	✓	✓	✓	✓	✓	—	—	✓	✓	✓	✓	✓	✓	✓	✓
P2	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓
P3	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓
P4	✓	✓	—	—	—	—	—	—	✓	✓	✓	✓	✓	✓	✓	✓
P5	—	✓	✓	✓	✓	✓	✓	✓	—	✓	✓	✓	✓	✓	✓	✓
P6	✓	✓	✓	✓	✓	✓	✓	—	✓	✓	✓	✓	✓	✓	✓	✓
P7	—	—	—	—	—	—	—	—	—	✓	✓	✓	✓	✓	✓	✓
P8	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓	✓
P9	—	—	—	—	—	—	✓	✓	—	—	—	—	—	—	✓	✓

Notes:
1. The symbol "✓" indicates a programmable I/O port.
2. The symbol "—" indicates the settings should be made as follows:
   - Set 0 to the corresponding bits in the PDi (i = 1, 4 to 7, 9) register. When read, the content is 0.
   - Set 0 to the corresponding bits in the Pi (i = 1, 4 to 7, 9) register. When read, the content is 0.
   - Set 0 to the corresponding bits in the P7DRR register. When read, the content is 0.

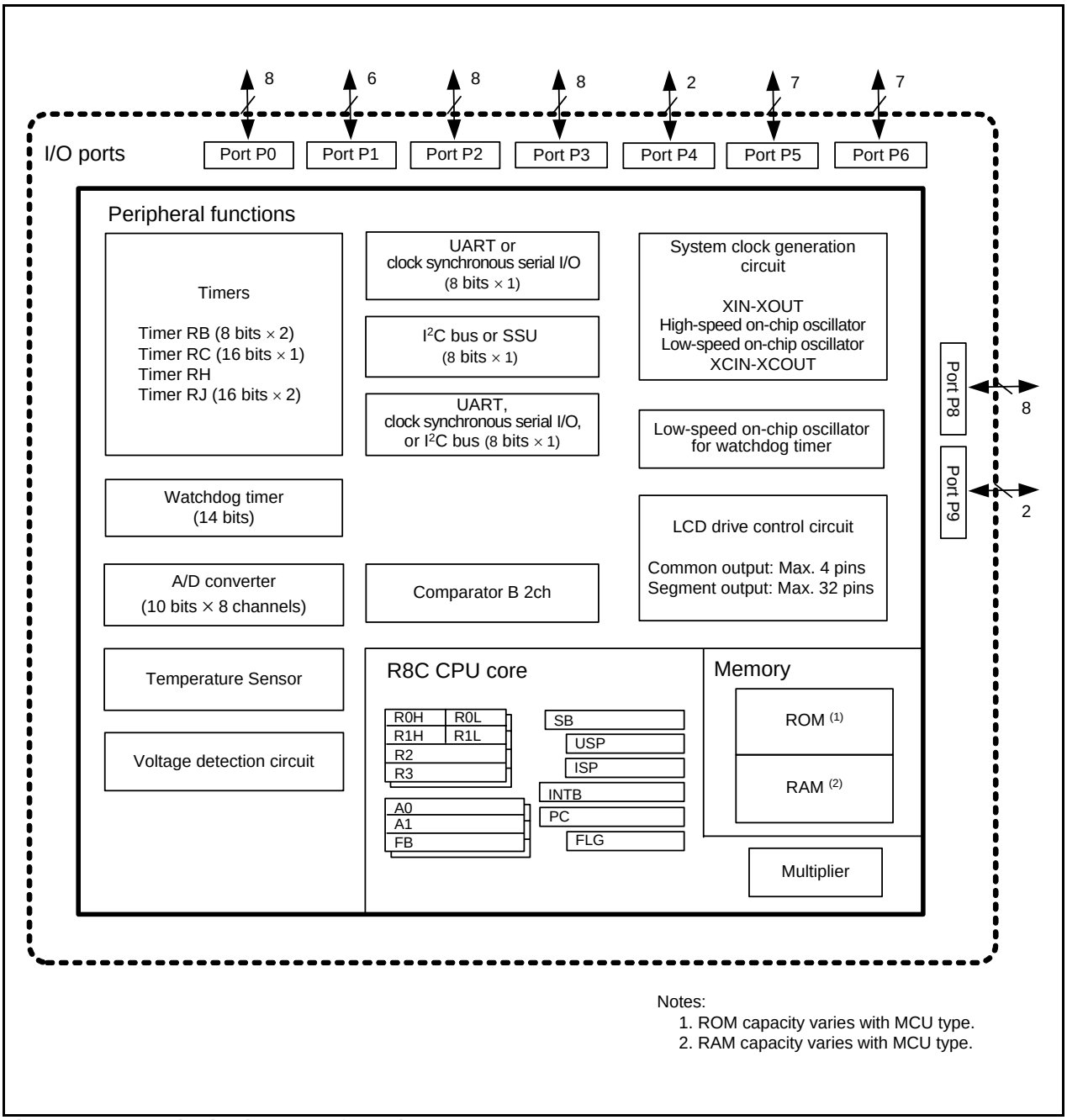
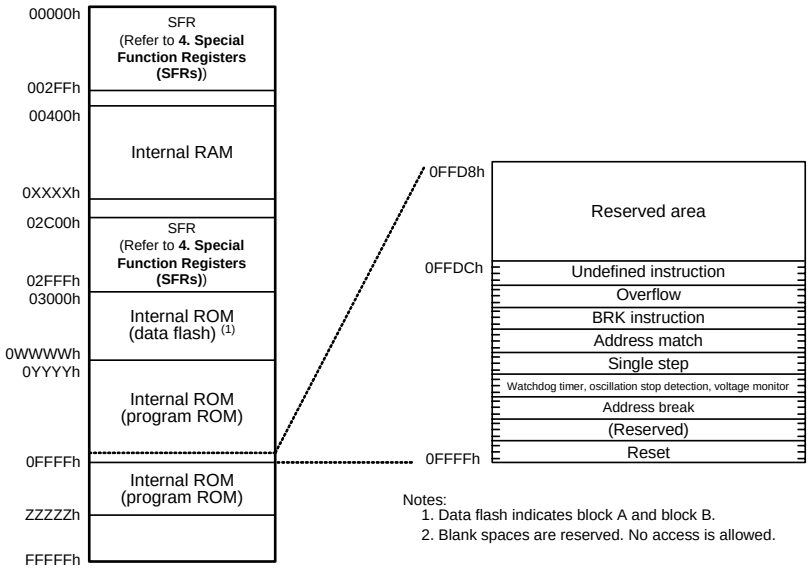


Figure 1.7 Block Diagram of R8C/LA6A Group

3. Memory

Figure 3.1 shows a Memory Map of each group. Each group has a 1-Mbyte address space from addresses 00000h to FFFFFh. For example, a 48-Kbyte internal ROM area is allocated addresses 04000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. The starting address of each interrupt routine is stored here.
The internal ROM (data flash) is allocated higher addresses, beginning with address 03000h.
For example, two 1-Kbyte internal ROM (data flash) areas are allocated addresses 03000h to 037FFh. Two 2-Kbyte internal RAM (data flash) areas are allocated addresses 03000h to 03FFFh.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 3.5-Kbyte internal RAM area is allocated addresses 00400h to 011FFh. The internal RAM is used not only for data storage but also as a stack area when a subroutine is called or when an interrupt request is acknowledged.
Special function registers (SFRs) are allocated addresses 00000h to 002FFh and 02C00h to 02FFFh. Peripheral function control registers are allocated here. All unallocated spaces within the SFRs are reserved and cannot be accessed by users.



Notes:
1. Data flash indicates block A and block B.
2. Blank spaces are reserved. No access is allowed.

Part Number	Internal ROM			Internal RAM		Data Flash	
	Capacity	Address 0YYYYh	Address ZZZZZh	Capacity	Address 0XXXXh	Capacity	Address 0WWWWh
R5F2LA32ANFP, R5F2LA32ADFP, R5F2LA52ANFP, R5F2LA52ADFP	8 Kbytes	0E000h	0FFFFh	2 Kbytes	00BFFh	1 Kbyte × 2	037FFh
R5F2LA34ANFP, R5F2LA34ADFP, R5F2LA54ANFP, R5F2LA54ADFP, R5F2LA64ANFP, R5F2LA64ANFA, R5F2LA64ADFP, R5F2LA64ADFA, R5F2LA84ANFP, R5F2LA84ANFA, R5F2LA84ADFP, R5F2LA84ADFA	16 Kbytes	0C000h	0FFFFh	2 Kbytes	00BFFh		
R5F2LA36ANFP, R5F2LA36ADFP, R5F2LA56ANFP, R5F2LA56ADFP, R5F2LA66ANFP, R5F2LA66ANFA, R5F2LA66ADFP, R5F2LA66ADFA, R5F2LA86ANFP, R5F2LA86ANFA, R5F2LA86ADFP, R5F2LA86ADFA	32 Kbytes	08000h	0FFFFh	2 Kbytes	00BFFh		
R5F2LA67ANFP, R5F2LA67ANFA, R5F2LA67ADFP, R5F2LA67ADFA, R5F2LA87ANFP, R5F2LA87ANFA, R5F2LA87ADFP, R5F2LA87ADFA	48 Kbytes	04000h	0FFFFh	3.5 Kbytes	011FFh		
R5F2LA38ANFP, R5F2LA38ADFP, R5F2LA58ANFP, R5F2LA58ADFP, R5F2LA68ANFP, R5F2LA68ANFA, R5F2LA68ADFP, R5F2LA68ADFA, R5F2LA88ANFP, R5F2LA88ANFA, R5F2LA88ADFP, R5F2LA88ADFA	64 Kbytes	04000h	13FFFh	3.5 Kbytes	011FFh		
R5F2LA6AANFP, R5F2LA6AANFA, R5F2LA6CADFP, R5F2LA6CADFA, R5F2LA8AANFP, R5F2LA8AANFA, R5F2LA8CADFP, R5F2LA8CADFA	96 Kbytes	04000h	1BFFFh	5.5 Kbytes	019FFh	2 Kbytes × 2	03FFFh
R5F2LA6AANFP, R5F2LA6AANFA, R5F2LA6CADFP, R5F2LA6CADFA, R5F2LA8AANFP, R5F2LA8AANFA, R5F2LA8CADFP, R5F2LA8CADFA	128 Kbytes	04000h	23FFFh	5.5 Kbytes	019FFh		

Figure 3.1 Memory Map

Table 4.2 SFR Information for R8C/LA5A Group (2) (1)

Address	Register	Symbol	After Reset
003Ah	Voltage Monitor 2 Circuit Control Register	VW2C	10000010b
003Bh			
003Ch			
003Dh			
003Eh			
003Fh			
0040h			
0041h	Flash Memory Ready Interrupt Control Register	FMRDYIC	XXXXX000b
0042h			
0043h	INT7 Interrupt Control Register	INT7IC	XX00X000b
0044h			
0045h	INT5 Interrupt Control Register	INT5IC	XX00X000b
0046h			
0047h	Timer RC Interrupt Control Register	TRCIC	XXXXX000b
0048h			
0049h			
004Ah	Timer RH Interrupt Control Register	TRHIC	XXXXX000b
004Bh			
004Ch			
004Dh	Key Input Interrupt Control Register	KUPIC	XXXXX000b
004Eh	A/D Conversion Interrupt Control Register	ADIC	XXXXX000b
004Fh	SSU Interrupt Control Register / IIC bus Interrupt Control Register (2)	SSUIC/IICIC	XXXXX000b
0050h			
0051h	UART0 Transmit Interrupt Control Register	S0TIC	XXXXX000b
0052h	UART0 Receive Interrupt Control Register	S0RIC	XXXXX000b
0053h			
0054h			
0055h	INT2 Interrupt Control Register	INT2IC	XX00X000b
0056h	Timer RJ0 Interrupt Control Register	TRJ0IC	XXXXX000b
0057h	Timer RB1 Interrupt Control Register	TRB1IC	XXXXX000b
0058h	Timer RB0 Interrupt Control Register	TRB0IC	XXXXX000b
0059h	INT1 Interrupt Control Register	INT1IC	XX00X000b
005Ah	INT3 Interrupt Control Register	INT3IC	XX00X000b
005Bh	Timer RJ1 Interrupt Control Register	TRJ1IC	XXXXX000b
005Ch			
005Dh	INT0 Interrupt Control Register	INT0IC	XX00X000b
005Eh			
005Fh			
0060h			
0061h			
0062h			
0063h			
0064h			
0065h			
0066h			
0067h			
0068h			
0069h			
006Ah	LCD Interrupt Control Register	LCDIC	XXXXX000b
006Bh			
006Ch			
006Dh			
006Eh			
006Fh			
0070h			
0071h			
0072h	Voltage monitor 1 Interrupt Control Register	VCMP1IC	XXXXX000b
0073h	Voltage monitor 2 Interrupt Control Register	VCMP2IC	XXXXX000b
0074h			
0075h			
0076h			
0077h			
0078h			
0079h			
007Ah			
007Bh			
007Ch			
007Dh			
007Eh			
007Fh			

X: Undefined

Notes:

1. Blank spaces are reserved. No access is allowed.
2. Selectable by the IICSEL bit in the SSUIICSR register.

Table 4.16 SFR Information for R8C/LA8A Group (7) (1)

Address	Register	Symbol	After Reset
0180h	Timer RJ Pin Select Register	TRJSR	00h
0181h	Timer RB Pin Select Register	TRBSR	00h
0182h	Timer RC Pin Select Register 0	TRCPSR0	00h
0183h	Timer RC Pin Select Register 1	TRCPSR1	00h
0184h			
0185h			
0186h			
0187h			
0188h	UART0 Pin Select Register	U0SR	00h
0189h			
018Ah	UART2 Pin Select Register 0	U2SR0	00h
018Bh	UART2 Pin Select Register 1	U2SR1	00h
018Ch	SSU/IIC Pin Select Register	SSUIICSR	00h
018Dh	Timer RH Second Interrupt Control Register	TRHICR	X0XXXXXXb 00000001b (3)
018Eh	INT Interrupt Input Pin Select Register	INTSR	00h
018Fh	I/O Function Pin Select Register	PINSR	00h
0190h			
0191h			
0192h			
0193h	SS Bit Counter Register	SSBR	11111000b
0194h	SS Transmit Data Register L / IIC bus Transmit Data Register (2)	SSTDR/ICDRT	FFh
0195h	SS Transmit Data Register H (2)	SSTDRH	FFh
0196h	SS Receive Data Register L / IIC bus Receive Data Register (2)	SSRDR/ICDRR	FFh
0197h	SS Receive Data Register H (2)	SSRDRH	FFh
0198h	SS Control Register H / IIC bus Control Register 1 (2)	SSCRH/ICCR1	00h
0199h	SS Control Register L / IIC bus Control Register 2 (2)	SSCRL/ICCR2	01111101b
019Ah	SS Mode Register / IIC bus Mode Register (2)	SSMR/ICMR	00010000b/00011000b
019Bh	SS Enable Register / IIC bus Interrupt Enable Register (2)	SSER/ICIER	00h
019Ch	SS Status Register / IIC bus Status Register (2)	SSSR/ICSR	00h/0000X000b
019Dh	SS Mode Register 2 / Slave Address Register (2)	SSMR2/SAR	00h
019Eh			
019Fh			
01A0h			
01A1h			
01A2h			
01A3h			
01A4h			
01A5h			
01A6h			
01A7h			
01A8h			
01A9h			
01AAh			
01ABh			
01ACh			
01ADh			
01AEh			
01AFh			
01B0h			
01B1h			
01B2h	Flash Memory Status Register	FST	10000X00b
01B3h			
01B4h	Flash Memory Control Register 0	FMR0	00h
01B5h	Flash Memory Control Register 1	FMR1	000000X0b
01B6h	Flash Memory Control Register 2	FMR2	00h
01B7h			
01B8h			
01B9h			
01BAh			
01BBh			
01BCh			
01BDh			
01BEh			
01BFh			

X: Undefined

Notes:

1. Blank spaces are reserved. No access is allowed.
2. Selectable by the IICSEL bit in the SSUIICSR register.
3. This is the reset value after reset by RTCRST bit in TRHCR register.

Table 5.7 Flash Memory (Program ROM) Characteristics
(V_{CC} = 1.8 to 5.5 V and T_{opr} = 0 to 60 °C, unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance (1)		10,000 (2)	–	–	times
–	Byte program time		–	80	–	µs
–	Block erase time		–	0.12	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	0.25 + CPU clock × 3 cycles	ms
–	Time from suspend until erase restart		–	–	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
–	Program, erase voltage		1.8	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time (6)	Ambient temperature = 85 °C	10	–	–	year

Notes:
1. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 1,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
2. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
3. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
4. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
5. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
6. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.8 Flash Memory (Data flash Block A and Block B) Characteristics (V_{CC} = 1.8 to 5.5 V and T_{opr} = −20 to 85 °C (N version)/ −40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance (1)		10,000 (2)	–	–	times
–	Byte program time (program/erase endurance ≤ 10,000 times)		–	150	–	µs
–	Block erase time (program/erase endurance ≤ 10,000 times)		–	0.05	1	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	0.25 + CPU clock × 3 cycles	ms
–	Time from suspend until erase restart		–	–	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
–	Program, erase voltage		1.8	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		−20 (6)	–	85	°C
–	Data hold time (7)	Ambient temperature = 85 °C	10	–	–	year

Notes:
1. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
2. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
3. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
4. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
5. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
6. −40 °C for D version.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

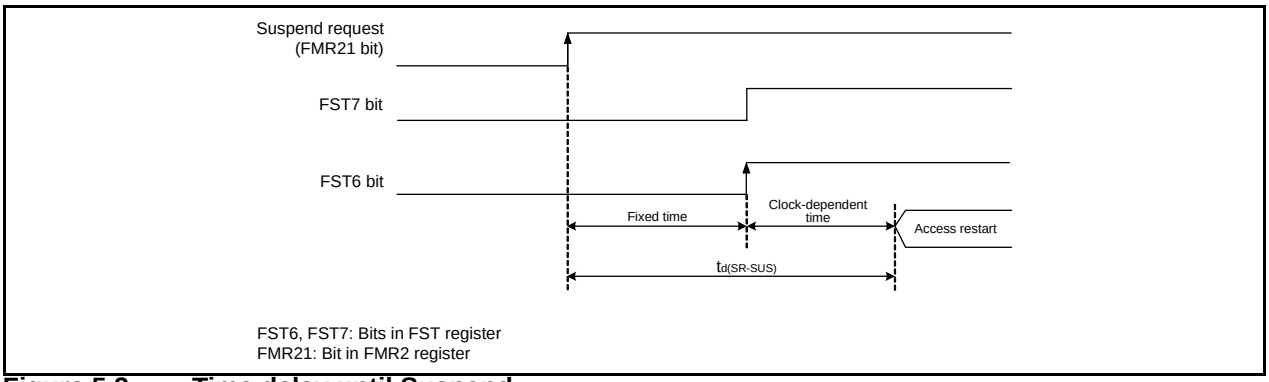


Figure 5.2 Time delay until Suspend

Table 5.13 High-speed On-Chip Oscillator Circuit Characteristics (VCC = 1.8 to 5.5 V and Topr = –20 to 85 °C (N version)/ –40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
–	High-speed on-chip oscillator frequency after reset	VCC = 1.8 V to 5.5 V – 20 °C ≤ Topr ≤ 85 °C	19.2	20	20.8	MHz
		VCC = 1.8 V to 5.5 V – 40 °C ≤ Topr ≤ 85 °C	19.0	20	21.0	MHz
	High-speed on-chip oscillator frequency when the FRA4 register correction value is written into the FRA1 register and the FRA5 register correction value into the FRA3 register (1)	VCC = 1.8 V to 5.5 V – 20 °C ≤ Topr ≤ 85 °C	17.694	18.432	19.169	MHz
		VCC = 1.8 V to 5.5 V – 40 °C ≤ Topr ≤ 85 °C	17.510	18.432	19.353	MHz
–	Oscillation stability time		–	5	30	µs
–	Self power consumption at oscillation	VCC = 5.0 V, Topr = 25 °C	–	530	–	µA

Note:
1. This enables the setting errors of bit rates such as 9600 bps and 38400 bps to be 0% when the serial interface is used in UART mode.

Table 5.14 Low-speed On-Chip Oscillator Circuit Characteristics (VCC = 1.8 to 5.5 V and Topr = –20 to 85 °C (N version)/ –40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		60	125	250	kHz
–	Oscillation stability time		–	–	35	µs
–	Self power consumption at oscillation	VCC = 5.0 V, Topr = 25°C	–	2	–	µA
fOCO-WDT	Low-speed on-chip oscillator frequency for the watchdog timer		60	125	250	kHz
–	Oscillation stability time		–	–	35	µs
–	Self power consumption at oscillation	VCC = 5.0 V, Topr = 25°C	–	2	–	µA

Table 5.15 Power Supply Circuit Characteristics (VCC = 1.8 to 5.5 V, Vss = 0 V, and Topr = 25 °C, unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
td(P-R)	Time for internal power supply stabilization during power-on (1)		–	–	2000	µs

Note:
1. Waiting time until the internal power supply generation circuit stabilizes during power-on.

5.1.4 DC Characteristics

Table 5.18 DC Characteristics (1) [4.0 V ≤ Vcc ≤ 5.5 V]
(Topr = –20 to 85 °C (N version)/ –40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter		Condition			Standard			Unit
						Min.	Typ.	Max.	
V_{OH}	Output “H” voltage		Port P8 (1)	V_{CC} = 5V	I_{OH} = –20 mA	V_{CC} – 2.0	–	V_{CC}	V
			Other pins	V_{CC} = 5V	I_{OH} = –5 mA	V_{CC} – 2.0	–	V_{CC}	V
V_{OL}	Output “L” voltage		Port P8 (1)	V_{CC} = 5V	I_{OL} = 20 mA	–	–	2.0	V
			Other pins	V_{CC} = 5V	I_{OL} = 5 mA	–	–	2.0	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{INT5}$, $\overline{INT7}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, $\overline{KI4}$, $\overline{KI5}$, $\overline{KI6}$, $\overline{KI7}$, TRCIOA, TRCIOB, TRCIOC, TRCIOD, TRJ0IO, TRJ1IO, $\overline{TRCTRG}$, TRCCLK, $\overline{ADTRG}$, RXD0, CLK0, SSI, SCL, SDA, SSO				0.05	0.5	–	V
		$\overline{RESET}$, $\overline{WKUP0}$				0.1	0.8	–	V
I_{IH}	Input “H” current		VI = 5 V, V_{CC} = 5 V			–	–	5.0	µA
I_{IL}	Input “L” current		VI = 0 V, V_{CC} = 5 V			–	–	–5.0	µA
R_{PULLUP}	Pull-up resistance		VI = 0 V, V_{CC} = 5 V			20	40	80	kΩ
R_{fXIN}	Feedback resistance	XIN				–	2.0	–	MΩ
R_{fXCIN}	Feedback resistance	XCIN				–	14	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode			1.8	–	–	V

Note:
1. This applies when the drive capacity of the output transistor is set to High by P8DRR register. When the drive capacity is set to Low, the value of any other pin applies.

5.2.3 Peripheral Function Characteristics

Table 5.32 A/D Converter Characteristics
(Vcc/AVcc = Vref = 1.8 to 5.5 V, Vss = 0 V, and Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter		Conditions		Standard			Unit
					Min.	Typ.	Max.	
–	Resolution		Vref = AVcc		–	–	10	Bit
–	Absolute accuracy (2)	10-bit mode	Vref = AVcc = 5.0 V	AN0 to AN11 input	–	–	±3	LSB
			Vref = AVcc = 2.2 V	AN0 to AN11 input	–	–	±5	LSB
			Vref = AVcc = 1.8 V	AN0 to AN11 input	–	–	±5	LSB
		8-bit mode	Vref = AVcc = 5.0 V	AN0 to AN11 input	–	–	±2	LSB
			Vref = AVcc = 2.2 V	AN0 to AN11 input	–	–	±2	LSB
			Vref = AVcc = 1.8 V	AN0 to AN11 input	–	–	±2	LSB
ϕAD	A/D conversion clock		4.0 ≤ Vref = AVcc ≤ 5.5 V (1)		1	–	20	MHz
			3.2 ≤ Vref = AVcc ≤ 5.5 V (1)		1	–	16	MHz
			2.7 ≤ Vref = AVcc ≤ 5.5 V (1)		1	–	10	MHz
			1.8 ≤ Vref = AVcc ≤ 5.5 V (1)		1	–	8	MHz
–	Tolerance level impedance				–	3	–	kΩ
tCONV	Conversion time	10-bit mode	Vref = AVcc = 5.0 V, ϕAD = 20 MHz		2.2	–	–	µs
		8-bit mode	Vref = AVcc = 5.0 V, ϕAD = 20 MHz		2.2	–	–	ms
tSAMP	Sampling time		ϕAD = 20 MHz		0.8	–	–	µs
IVref	Vref current		Vcc = 5 V, XIN = f1 = ϕAD = 20 MHz		-	45	–	µA
Vref	Reference voltage				1.8	–	AVcc	V
VIA	Analog input voltage (3)				0	–	Vref	V
OCVREF	On-chip reference voltage		2 MHz ≤ ϕAD ≤ 4 MHz		1.53	1.70	1.87	V

Notes:
1. The A/D conversion result will be undefined in wait mode, stop mode, power-off mode, when the flash memory stops, and in low-current-consumption mode. Do not perform A/D conversion in these states or transition to these states during A/D conversion.
2. This applies when the peripheral functions are stopped.
3. When the analog input voltage is over the reference voltage, the A/D conversion result will be 3FFh in 10-bit mode and FFh in 8-bit mode.

Table 5.33 Temperature Sensor Characteristics
(VSS = 0 V and Topr = –20 to 85 °C (N version)/–40 to 85 °C (D version), unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
VTMP	Temperature sensor output voltage	1.8 V ≤ Vref = AVcc ≤ 5.5 V ϕAD = 1.0 MHz to 5.0 MHz Ambient temperature = 25 °C	550	600	650	mV
–	Temperature coefficient	1.8 V ≤ Vref = AVcc ≤ 5.5 V ϕAD = 1.0 MHz to 5.0 MHz Ambient temperature = 25 °C	–	–2.1	–	mV/°C
–	Start-up time	1.8 V ≤ Vref = AVcc ≤ 5.5 V ϕAD = 1.0 MHz to 5.0 MHz	–	–	200	µs
ITMP	Operating current	1.8 V ≤ Vref = AVcc ≤ 5.5 V ϕAD = 1.0 MHz to 5.0 MHz	–	100	–	µA

Table 5.37 Flash Memory (Data flash Block A and Block B) Characteristics (Vcc = 1.8 to 5.5 V and Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance (1)		10,000 (2)	–	–	times
–	Byte program time (program/erase endurance ≤ 10,000 times)		–	150	–	µs
–	Block erase time (program/erase endurance ≤ 10,000 times)	Internal ROM Capacity: 1 KB × 2	–	0.05	1	s
		Internal ROM Capacity: 2 KB × 2	–	0.055	1	s
$t_{d(SR-SUS)}$	Time delay from suspend request until suspend		–	–	0.25 + CPU clock × 3 cycles	ms
–	Time from suspend until erase restart		–	–	30 + CPU clock × 1 cycle	µs
$t_{d(CMDRST-READY)}$	Time from when command is forcibly terminated until reading is enabled		–	–	30 + CPU clock × 1 cycle	µs
–	Program, erase voltage		1.8	–	5.5	V
–	Read voltage		1.8	–	5.5	V
–	Program, erase temperature		–20 (6)	–	85	°C
–	Data hold time (7)	Ambient temperature = 85 °C	10	–	–	year

Notes:
1. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times. For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one.
   However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
2. Endurance to guarantee all electrical characteristics after program and erase. (1 to Min. value can be guaranteed).
3. In a system that executes multiple programming operations, the actual erasure count can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
4. If an error occurs during block erase, attempt to execute the clear status register command, then execute the block erase command at least three times until the erase error does not occur.
5. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
6. –40°C for D version.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

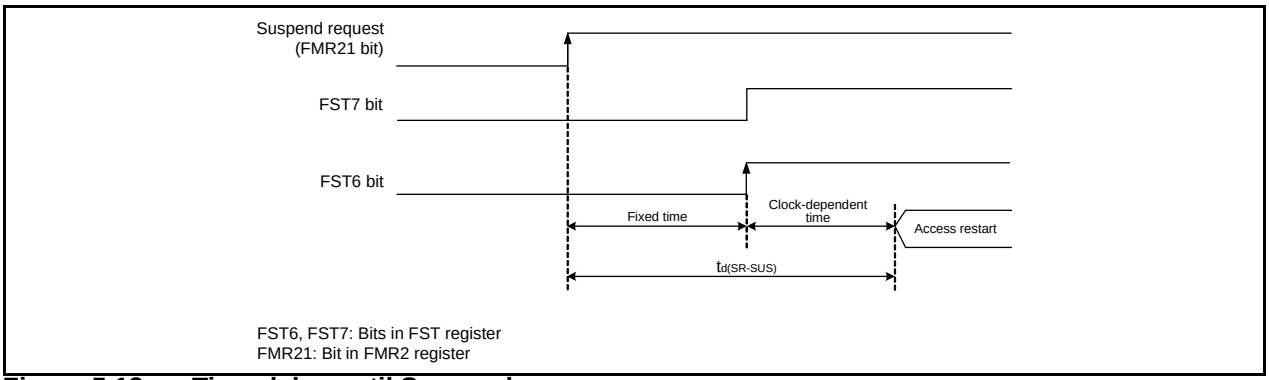


Figure 5.13 Time delay until Suspend

Table 5.40 Voltage Detection 2 Circuit Characteristics
(V_{CC} = 1.8 to 5.5 V and T_{opr} = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

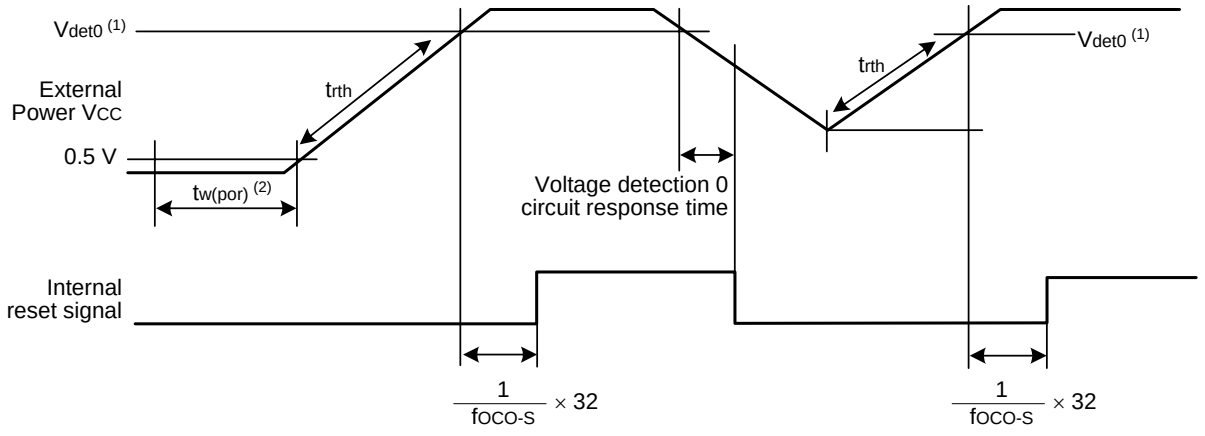
Symbol	Parameter	Condition		Standard			Unit
				Min.	Typ.	Max.	
V_{det2}	Voltage detection level Vdet2_0 (1)	At the falling of V_{CC}		3.70	4.0	4.30	V
–	Hysteresis width at the rising of Vcc in voltage detection 2 circuit			–	0.10	–	V
–	Voltage detection 2 circuit response time (2)	In operation	At the falling of Vcc from 5 V to (Vdet2_0 – 0.1) V	–	20	150	µs
		In stop mode	At the falling of Vcc from 5 V to (Vdet2_0 – 0.1) V	–	200	500	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0 V		–	1.7	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts (3)			–	–	100	µs

Notes:
1. The voltage detection level varies with detection targets. Select the level with the VCA24 bit in the VCA2 register.
2. Time until the voltage monitor 2 interrupt request is generated after the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates after setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.

Table 5.41 Power-on Reset Circuit Characteristics (1)
(T_{opr} = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
t_{rth}	External power V_{CC} rise gradient		0	–	50000	mV/ms

Note:
1. To use the power-on reset function, enable voltage monitor 0 reset by setting the LVDAS bit in the OFS register to 0.



Notes:
1. V_{det0} indicates the voltage detection level of the voltage detection 0 circuit. Refer to **6. Voltage Detection Circuit** in the User's Manual: Hardware for details.
2. $t_{w(por)}$ indicates the duration the external power V_{CC} must be held below the valid voltage (0.5 V) to enable a power-on reset. When turning on the power after it falls with voltage monitor 0 reset disabled, maintain $t_{w(por)}$ for 1 ms or more.

Figure 5.14 Power-on Reset Circuit Characteristics

Table 5.48 DC Characteristics (2) [4.0 V ≤ Vcc ≤ 5.5 V]
(Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition								Standard			Unit
			Oscillation Circuit		On-Chip Oscillator		CPU Clock	Low-Power-Consumption Setting	Other	Min.	Typ. (3)	Max.	
			XIN (2)	XCIN	High-Speed	Low-Speed							
Icc	Power supply current (1)	High-speed clock mode	20 MHz	Off	Off	125 kHz	No division	–		–	4.7	10	mA
			16 MHz	Off	Off	125 kHz	No division	–		–	3.9	8	mA
			10 MHz	Off	Off	125 kHz	No division	–		–	2.3	–	mA
			20 MHz	Off	Off	Off	No division	FMR27 = 1 MSTCR0 = BEh MSTCR1 = 3Fh	Flash memory off Program operation on RAM Module standby setting enabled	–	3.1	–	mA
			20 MHz	Off	Off	125 kHz	Divide-by-8	–		–	1.8	–	mA
			16 MHz	Off	Off	125 kHz	Divide-by-8	–		–	1.5	–	mA
			10 MHz	Off	Off	125 kHz	Divide-by-8	–		–	1.0	–	mA
		High-speed on-chip oscillator mode	Off	Off	20 MHz	125 kHz	No division	–		–	5.0	11	mA
			Off	Off	20 MHz	125 kHz	Divide-by-8	–		–	2.1	–	mA
			Off	Off	4 MHz	125 kHz	Divide-by-16	MSTCR0 = BEh MSTCR1 = 3Fh		–	0.9	–	mA
		Low-speed on-chip oscillator mode	Off	Off	Off	125 kHz	No division	FMR27 = 1 VCA20 = 0		–	110	320	µA
			Off	Off	Off	125 kHz	Divide-by-8	FMR27 = 1 VCA20 = 0		–	63	220	µA
		Low-speed clock mode	Off	32 kHz	Off	Off	No division	FMR27 = 1 VCA20 = 0		–	60	220	µA
			Off	32 kHz	Off	Off	No division	FMSTP = 1 VCA20 = 0	Flash memory off Program operation on RAM	–	46	–	µA
		Wait mode	Off	Off	Off	125 kHz	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1	While a WAIT instruction is executed Peripheral clock operation	–	9.0	50	µA
			Off	Off	Off	125 kHz	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off	–	2.8	33	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 0	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode LCD drive control circuit (4) When external division resistors are used	–	4.6	–	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode	–	2.4	–	µA
		Stop mode	Off	Off	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Topr = 25°C Peripheral clock off	–	0.5	2.2	µA
			Off	Off	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Topr = 85°C Peripheral clock off	–	1.2	–	µA
		Power-off mode	Off	Off	Off	Off	–	–	Power-off 0 Topr = 25°C	–	0.01	0.1	µA
			Off	Off	Off	Off	–	–	Power-off 0 Topr = 85°C	–	0.03	–	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 25°C	–	1.8	6.4	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 85°C	–	2.7	–	µA

Notes:
1. Vcc = 4.0 V to 5.5 V, single chip mode, output pins are open, and other pins are Vss.
2. XIN is set to square wave input.
3. Vcc = 5.0 V
4. VLCD = Vcc, external division resistors are used for VL3 to VL1, 1/3 bias, 1/4 duty, f(FR) = 64 Hz, SEG0 to SEG39 are selected, and segment and common output pins are open. The standard value does not include the current that flows through external division resistors.

Table 5.50 DC Characteristics (4) [2.7 V ≤ Vcc < 4.0 V]
(Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition								Standard			Unit
			Oscillation Circuit		On-Chip Oscillator		CPU Clock	Low-Power-Consumption Setting	Other	Min.	Typ. (3)	Max.	
			XIN (2)	XCIN	High-Speed	Low-Speed							
Icc	Power supply current (1)	High-speed clock mode	20 MHz	Off	Off	125 kHz	No division	–		–	4.7	10	mA
			10 MHz	Off	Off	125 kHz	No division	–		–	2.3	6	mA
			20 MHz	Off	Off	Off	No division	FMR27 = 1 MSTCR0 = BEh MSTCR1 = 3Fh	Flash memory off Program operation on RAM Module standby setting enabled	–	2.9	–	mA
			20 MHz	Off	Off	125 kHz	Divide-by-8	–		–	1.8	–	mA
			10 MHz	Off	Off	125 kHz	Divide-by-8	–		–	1.0	–	mA
		High-speed on-chip oscillator mode	Off	Off	20 MHz	125 kHz	No division	–		–	5.0	11	mA
			Off	Off	20 MHz	125 kHz	Divide-by-8	–		–	2.1	–	mA
			Off	Off	10 MHz	125 kHz	No division	–		–	2.9	–	mA
			Off	Off	10 MHz	125 kHz	Divide-by-8	–		–	1.5	–	mA
			Off	Off	4 MHz	125 kHz	Divide-by-16	MSTCR0 = BEh MSTCR1 = 3Fh		–	0.9	–	mA
		Low-speed on-chip oscillator mode	Off	Off	Off	125 kHz	No division	FMR27 = 1 VCA20 = 0		–	106	300	µA
			Off	Off	Off	125 kHz	Divide-by-8	FMR27 = 1 VCA20 = 0		–	54	200	µA
		Low-speed clock mode	Off	32 kHz	Off	Off	No division	FMR27 = 1 VCA20 = 0		–	54	200	µA
			Off	32 kHz	Off	Off	No division	FMSTP = 1 VCA20 = 0	Flash memory off Program operation on RAM	–	36	–	µA
		Wait mode	Off	Off	Off	125 kHz	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1	While a WAIT instruction is executed Peripheral clock operation	–	9.0	50	µA
			Off	Off	Off	125 kHz	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off	–	2.5	31	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 0	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode LCD drive control circuit (4) When external division resistors are used	–	3.1	–	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode	–	1.7	–	µA
		Stop mode	Off	Off	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Topr = 25°C Peripheral clock off	–	0.5	2.2	µA
			Off	Off	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Topr = 85°C Peripheral clock off	–	1.2	–	µA
		Power-off mode	Off	Off	Off	Off	–	–	Power-off 0 Topr = 25°C	–	0.01	0.1	µA
			Off	Off	Off	Off	–	–	Power-off 0 Topr = 85°C	–	0.02	–	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 25°C	–	1.3	4.5	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 85°C	–	2.2	–	µA

Notes:
1. Vcc = 2.7 V to 4.0 V, single chip mode, output pins are open, and other pins are Vss.
2. XIN is set to square wave input.
3. Vcc = 3.0 V
4. VLCD = Vcc, external division resistors are used for VL3 to VL1, 1/3 bias, 1/4 duty, f(FR) = 64 Hz, SEG0 to SEG39 are selected, and segment and common output pins are open. The standard value does not include the current that flows through external division resistors.

Table 5.52 DC Characteristics (6) [1.8 V ≤ Vcc < 2.7 V]
(Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition								Standard			Unit
			Oscillation Circuit		On-Chip Oscillator		CPU Clock	Low-Power-Consumption Setting	Other	Min.	Typ. (3)	Max.	
			XIN (2)	XCIN	High-Speed	Low-Speed							
Icc	Power supply current (1)	High-speed clock mode	8 MHz	Off	Off	125 kHz	No division	–		–	2.1	–	mA
			8 MHz	Off	Off	125 kHz	Divide-by-8	–		–	0.9	–	mA
		High-speed on-chip oscillator mode	Off	Off	5 MHz	125 kHz	No division	–		–	1.8	5	mA
			Off	Off	5 MHz	125 kHz	Divide-by-8	–		–	1.1	–	mA
			Off	Off	4 MHz	125 kHz	Divide-by-16	MSTCR0 = BEh MSTCR1 = 3Fh		–	0.9	–	mA
		Low-speed on-chip oscillator mode	Off	Off	Off	125 kHz	No division	FMR27 = 1 VCA20 = 0		–	106	300	µA
			Off	Off	Off	125 kHz	Divide-by-8	FMR27 = 1 VCA20 = 0		–	54	200	µA
		Low-speed clock mode	Off	32 kHz	Off	Off	No division	FMR27 = 1 VCA20 = 0		–	54	200	µA
			Off	32 kHz	Off	Off	No division	FMSTP = 1 VCA20 = 0	Flash memory off Program operation on RAM	–	36	–	µA
		Wait mode	Off	Off	Off	125 kHz	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1	While a WAIT instruction is executed Peripheral clock operation	–	9.0	50	µA
			Off	Off	Off	125 kHz	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off	–	2.5	31	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 0	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode LCD drive control circuit (4) When external division resistors are used	–	2.4	–	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 VCA20 = 1 CM02 = 1 CM01 = 1	While a WAIT instruction is executed Peripheral clock off Timer RH operation in real-time clock mode	–	1.7	–	µA
		Stop mode	Off	Off	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Topr = 25°C Peripheral clock off	–	0.5	2.2	µA
			Off	Off	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Topr = 85°C Peripheral clock off	–	1.2	–	µA
		Power-off mode	Off	Off	Off	Off	–	–	Power-off 0 Topr = 25°C	–	0.01	0.1	µA
			Off	Off	Off	Off	–	–	Power-off 0 Topr = 85°C	–	0.02	–	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 25°C	–	1.2	4	µA
			Off	32 kHz	Off	Off	–	VCA27 = 0 VCA26 = 0 VCA25 = 0 CM10 = 1	Power-off 2 Topr = 85°C	–	2	–	µA

Notes:
1. Vcc = 1.8 V to 2.7 V, single chip mode, output pins are open, and other pins are Vss.
2. XIN is set to square wave input.
3. Vcc = 2.2 V
4. VLCD = Vcc, external division resistors are used for VL3 to VL1, 1/3 bias, 1/4 duty, f(FR) = 64 Hz, SEG0 to SEG39 are selected, and segment and common output pins are open.The standard value does not include the current that flows through external division resistors.

5.2.5 AC Characteristics

Table 5.53 Timing Requirements of Synchronous Serial Communication Unit (SSU) (V_{CC} = 1.8 to 5.5 V, V_{SS} = 0 V, and T_{opr} = −20 to 85°C (N version)/ −40 to 85°C (D version), unless otherwise specified.)

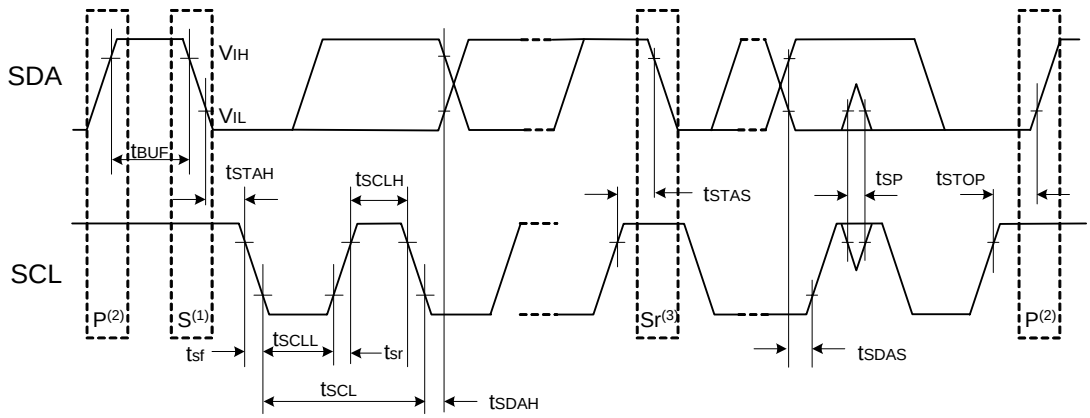
Symbol	Parameter		Conditions	Standard			Unit
				Min.	Typ.	Max.	
t_{SUCYC}	SSCK clock cycle time			4	–	-	t_{CYC} (1)
t_{HI}	SSCK clock “H” width			0.4	–	0.6	t_{SUCYC}
t_{LO}	SSCK clock “L” width			0.4	–	0.6	t_{SUCYC}
t_{RISE}	SSCK clock rising time	Master		–	–	1	t_{CYC} (1)
		Slave		–	–	1	µs
t_{FALL}	SSCK clock falling time	Master		–	–	1	t_{CYC} (1)
		Slave		–	–	1	µs
t_{SU}	SSO, SSI data input setup time			100	–	–	ns
t_H	SSO, SSI data input hold time			1	–	–	t_{CYC} (1)
t_{LEAD}	$\overline{SCS}$ setup time	Slave		1t_{CYC} + 50	–	–	ns
t_{LAG}	$\overline{SCS}$ hold time	Slave		1t_{CYC} + 50	–	–	ns
t_{OD}	SSO, SSI data output delay time			–	–	1t_{CYC} + 20	ns
t_{SA}	SSI slave access time		2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	1.5t_{CYC} + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	–	–	1.5t_{CYC} + 200	ns
t_{OR}	SSI slave out open time		2.7 V ≤ V_{CC} ≤ 5.5 V	–	–	1.5t_{CYC} + 100	ns
			1.8 V ≤ V_{CC} < 2.7 V	–	–	1.5t_{CYC} + 200	ns

Note:
1. 1t_{CYC} = 1/f1(s)

Table 5.54 Timing Requirements of I²C bus Interface (1)
(Vcc = 1.8 to 5.5 V, Vss = 0 V, and Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
tSCL	SCL input cycle time		12tCYC + 600 (1)	–	–	ns
tSCLH	SCL input “H” width		3tCYC + 300 (1)	–	–	ns
tSCLL	SCL input “L” width		5tCYC + 500 (1)	–	–	ns
tsf	SCL, SDA input fall time		–	–	300	ns
tSP	SCL, SDA input spike pulse rejection time		–	–	1tCYC (1)	ns
tBUF	SDA input bus-free time		5tCYC (1)	–	–	ns
tSTAH	Start condition input hold time		3tCYC (1)	–	–	ns
tSTAS	Retransmit start condition input setup time		3tCYC (1)	–	–	ns
tSTOP	Stop condition input setup time		3tCYC (1)	–	–	ns
tSDAS	Data input setup time		1tCYC + 40 (1)	–	–	ns
tSDAH	Data input hold time		10	–	–	ns

Note:
1. 1tCYC = 1/f1(s)



Notes:
1. Start condition
2. Stop condition
3. Retransmit start condition

Figure 5.18 I/O Timing of I²C bus Interface

Table 5.55 Timing Requirements of External Clock Input (XIN, XCIN)
(Vss = 0 V and Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Standard						Unit
		Vcc = 2.2V, Topr = 25°C		Vcc = 3V, Topr = 25°C		Vcc = 5V, Topr = 25°C		
		Min.	Max.	Min.	Max.	Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	200	–	50	–	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	90	–	24	–	24	–	ns
$t_{WL(XIN)}$	XIN input “L” width	90	–	24	–	24	–	ns
$t_{c(XCIN)}$	XCIN input cycle time	20	–	20	–	20	–	µs
$t_{WH(XCIN)}$	XCIN input “H” width	10	–	10	–	10	–	µs
$t_{WL(XCIN)}$	XCIN input “L” width	10	–	10	–	10	–	µs

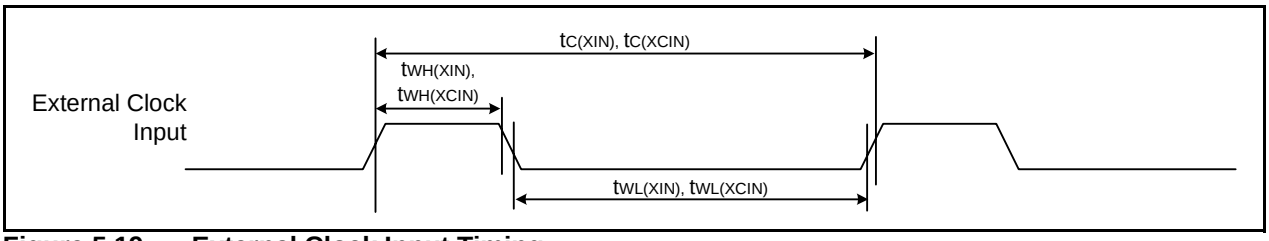


Figure 5.19 External Clock Input Timing

Table 5.56 Timing Requirements of TRJiIO (i = 0 to 2)
(Vss = 0 V and Topr = –20 to 85°C (N version)/ –40 to 85°C (D version), unless otherwise specified.)

Symbol	Parameter	Standard						Unit
		Vcc = 2.2V, Topr = 25°C		Vcc = 3V, Topr = 25°C		Vcc = 5V, Topr = 25°C		
		Min.	Max.	Min.	Max.	Min.	Max.	
$t_{c(TRJIO)}$	TRJiIO input cycle time	500	–	300	–	100	–	ns
$t_{WH(TRJIO)}$	TRJiIO input “H” width	200	–	120	–	40	–	ns
$t_{WL(TRJIO)}$	TRJiIO input “L” width	200	–	120	–	40	–	ns

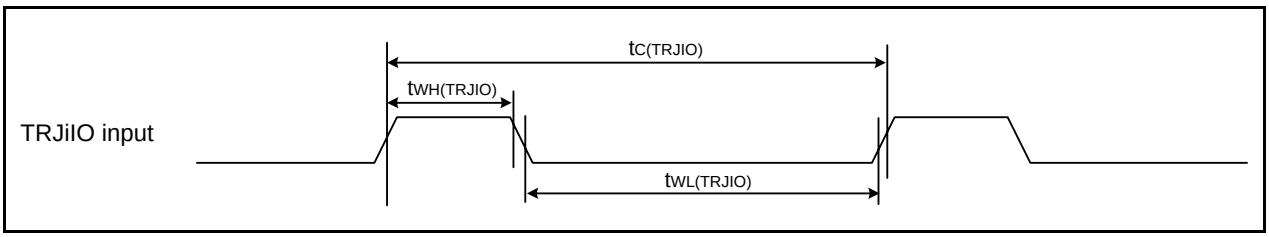


Figure 5.20 Input Timing of TRJiIO

General Precautions in the Handling of MPU/MCU Products

The following usage notes are applicable to all MPU/MCU products from Renesas. For detailed usage notes on the products covered by this manual, refer to the relevant sections of the manual. If the descriptions under General Precautions in the Handling of MPU/MCU Products and in the body of the manual differ from each other, the description in the body of the manual takes precedence.

1. Handling of Unused Pins

   Handle unused pins in accord with the directions given under Handling of Unused Pins in the manual.

   — The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible. Unused pins should be handled as described under Handling of Unused Pins in the manual.

2. Processing at Power-on

   The state of the product is undefined at the moment when power is supplied.

   — The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the moment when power is supplied.

   In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the moment when power is supplied until the reset process is completed.

   In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the moment when power is supplied until the power reaches the level at which resetting has been specified.

3. Prohibition of Access to Reserved Addresses

   Access to reserved addresses is prohibited.

   — The reserved addresses are provided for the possible future expansion of functions. Do not access these addresses; the correct operation of LSI is not guaranteed if they are accessed.

4. Clock Signals

   After applying a reset, only release the reset line after the operating clock signal has become stable. When switching the clock signal during program execution, wait until the target clock signal has stabilized.

   — When the clock signal is generated with an external resonator (or from an external oscillator) during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Moreover, when switching to a clock signal produced with an external resonator (or by an external oscillator) while program execution is in progress, wait until the target clock signal is stable.

5. Differences between Products

   Before changing from one product to another, i.e. to one with a different part number, confirm that the change will not lead to problems.

   — The characteristics of MPU/MCU in the same group but having different part numbers may differ because of the differences in internal memory capacity and layout pattern. When changing to products of different part numbers, implement a system-evaluation test for each of the products.

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